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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re New National Phase Patent Application of)
Shin HASHIMOTO et al.)
International Application No. PCT/JP00/06851) Attn: US/DO/EO
International Filing Date: October 3, 2000)
For: METHOD FOR FABRICATING)
SEMICONDUCTOR DEVICE) Date: May 25, 2001

PRELIMINARY AMENDMENT

Honorable Commissioner for Patents
Washington, D.C. 20231

Sir:

Please preliminarily amend the subject application as follows:

IN THE SPECIFICATION:

Please amend the specification as follows: Please note that specification is presented below in its amended form. It is further presented as an Attachment to the Amendment whereby the amendments to the specification are outlined using the conventional method of bracketing and underlining.

Please amend the specification starting at page 17, line 23 through page 18, line 2 as follows:

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Next, sputtering is carried out in a sputtering system having a chamber kept at a vacuum of 1×10^{-5} through 1×10^{-7} Pa, so as to deposit a metal film, such as a cobalt film 110, on the entire surface of the semiconductor substrate 100 as is shown in FIG. 3(c).